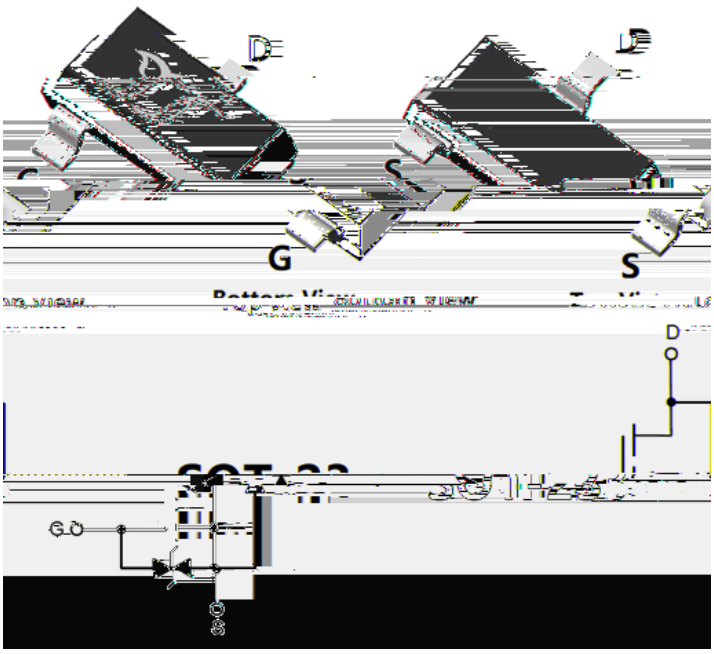
N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 60V
- I_D 0.6A
- $R_{DS(ON)}$(at V_{GS}=10V) 1.5Ω
- $R_{DS(ON)}$(at V_{GS}=4.5V) 1.8Ω
- $R_{DS(ON)}$(at V_{GS}=2.5V) 3.7Ω
- $R_{DS(ON)}$(at V_{GS}=1.8V) 8.5Ω
- Gate-Source ESD Rating Up to 2KV (HBM)

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface TTL/CMOS

■ Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25	I_D	0.6	A
	T_A=100		0.38	
Pulsed Drain Current [A]		I_{DM}	1.5	A
Total Power Dissipation [B]	T_A=25	P_D	0.8	W
	T_A=100		0.3	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 +150	

■Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient [C]	Steady-State	$R_{\theta JA}$	120	150	/W

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS138KJ	F2	BK	3000	30000	120000	7“ reel

■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V	-	-	1	μA
		V_{DS}=60V, V_{GS}=0V, Tj=150				

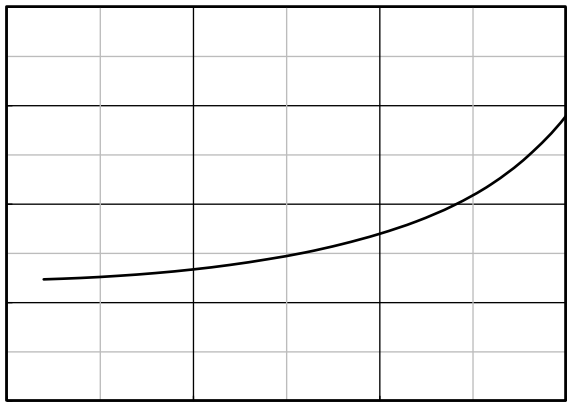


Figure 7. $R_{DS(on)}$ VS Drain Current

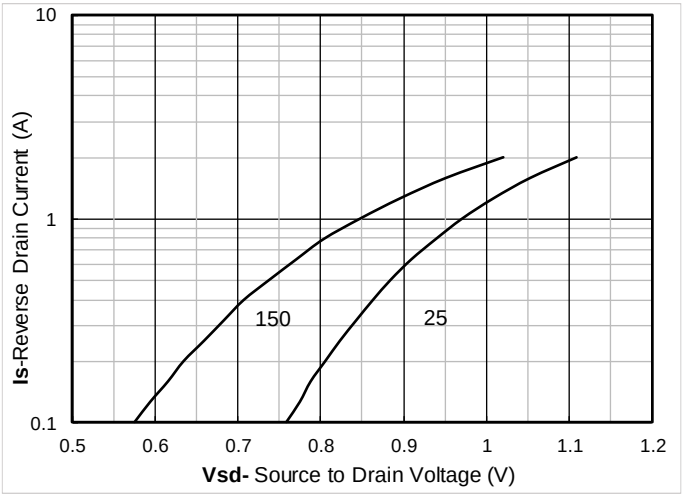


Figure 8. Forward characteristics of reverse diode

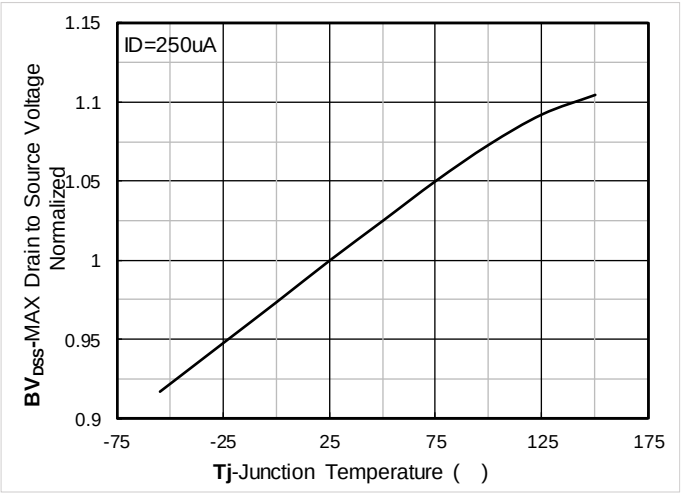


Figure 9. Normalized breakdown voltage

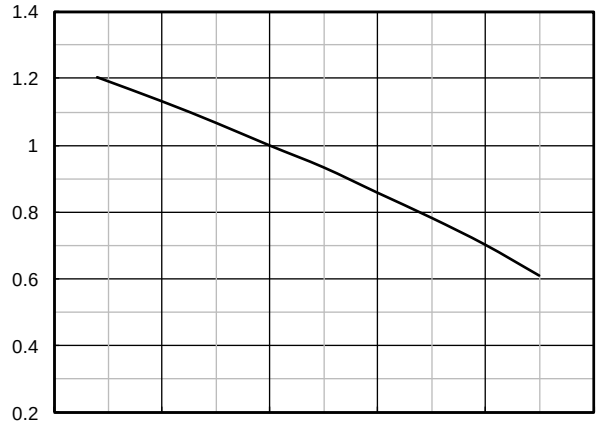


Figure 10. Normalized Threshold voltage

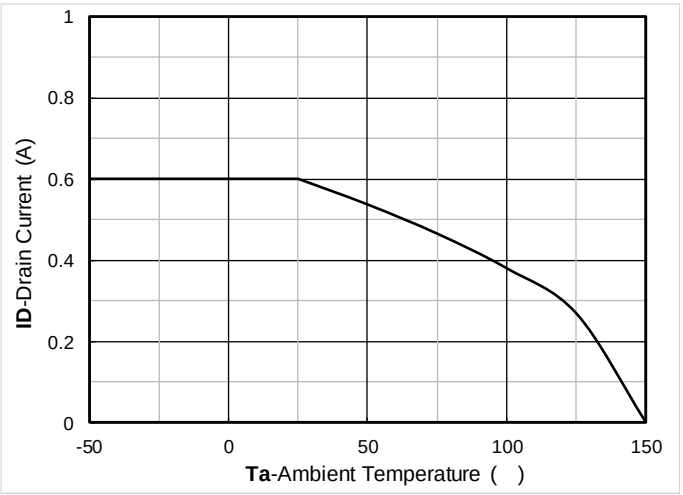


Figure 11. Current dissipation

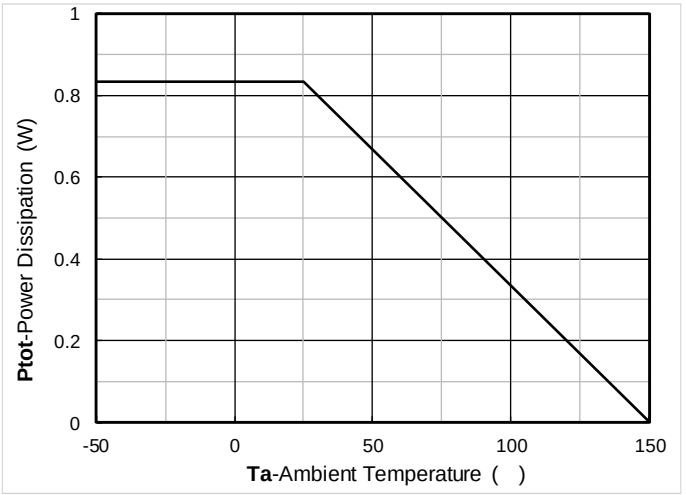


Figure 12. Power dissipation

Figure 13. Maximum Transient Thermal Impedance

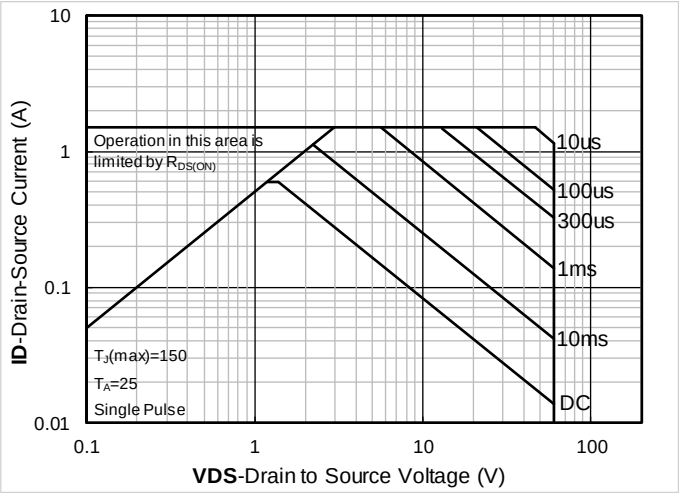


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

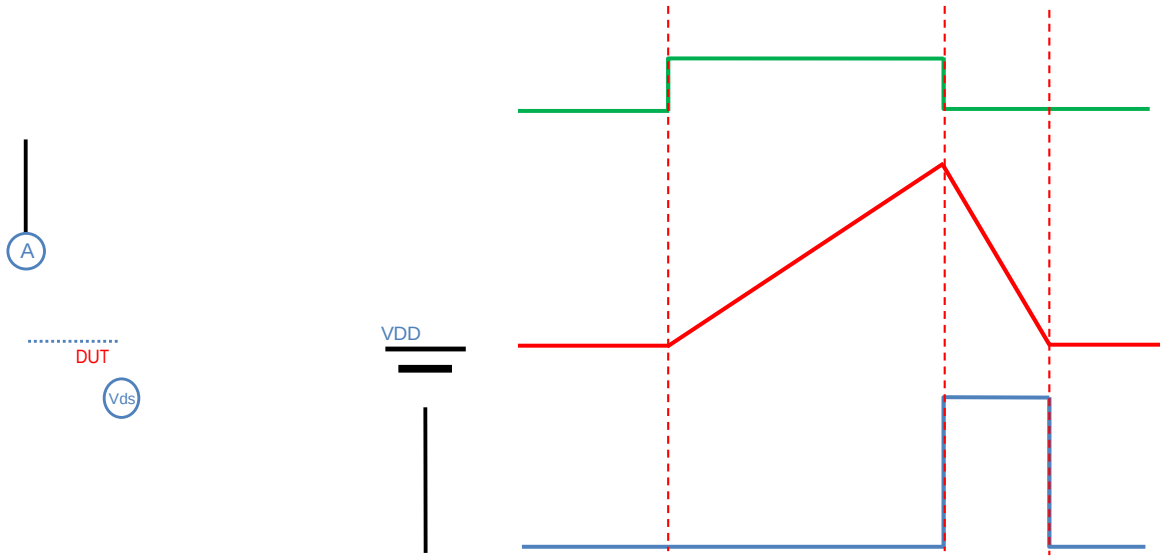


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

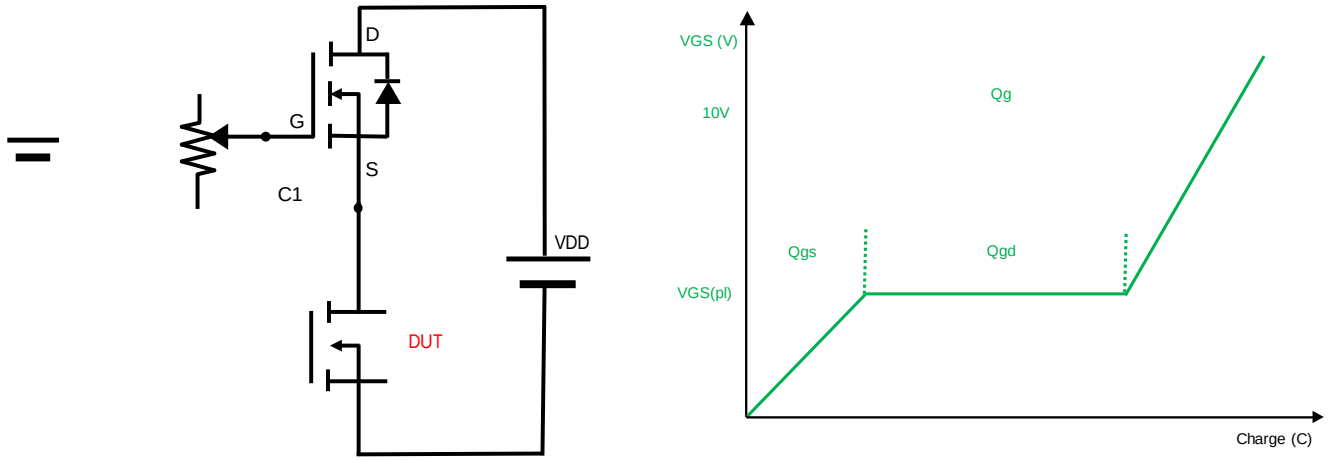


Figure B. Gate Charge Test Circuit & Waveform

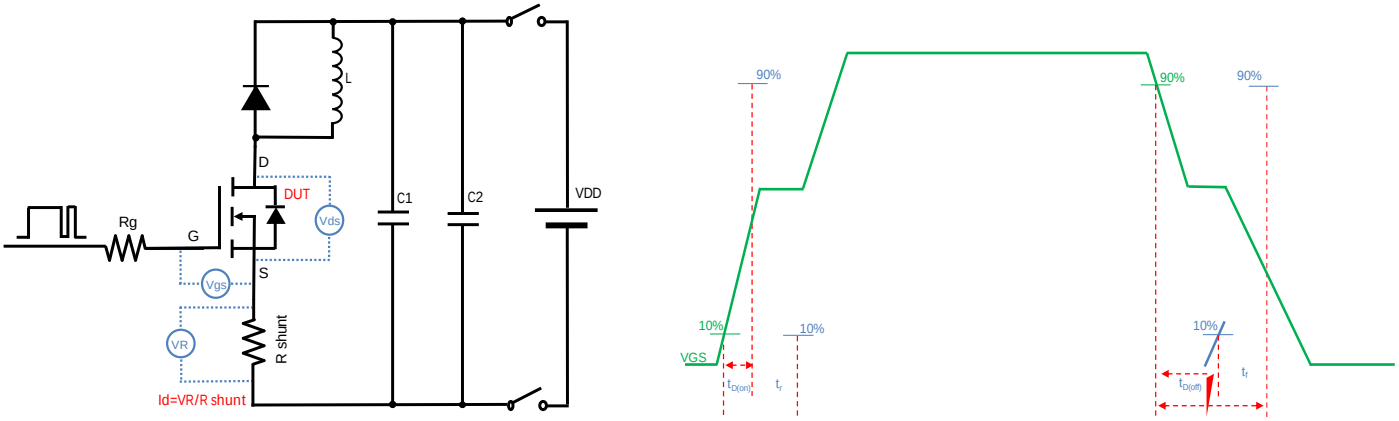


Figure C. Resistive Switching Test Circuit & Waveform

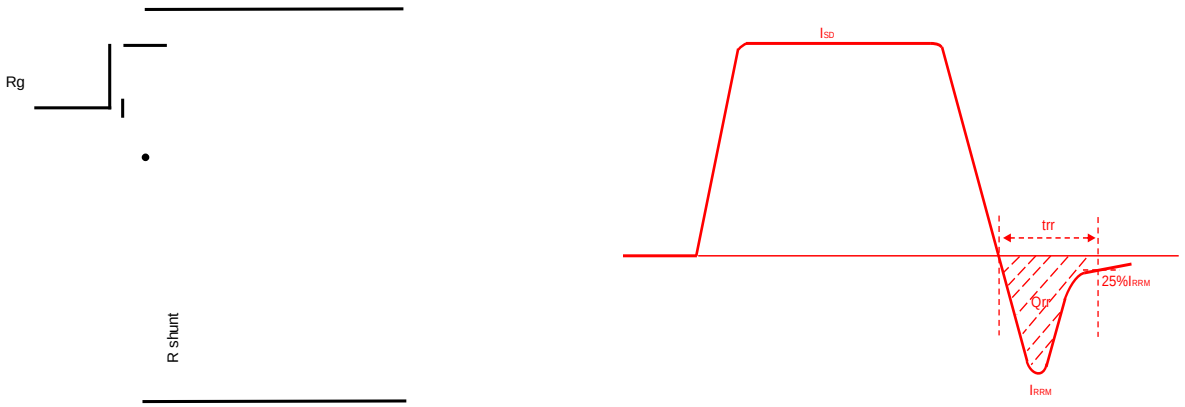
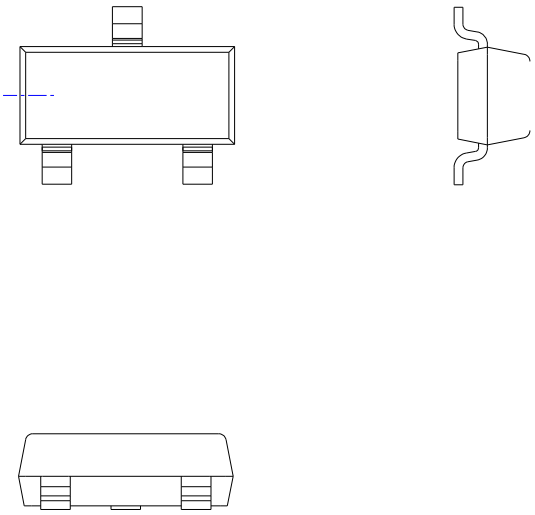


Figure D. Diode Recovery Test Circuit & Waveform

■ SOT-23 Package information



UNIT mm

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